

P-Channel MOSFET

Product Summary

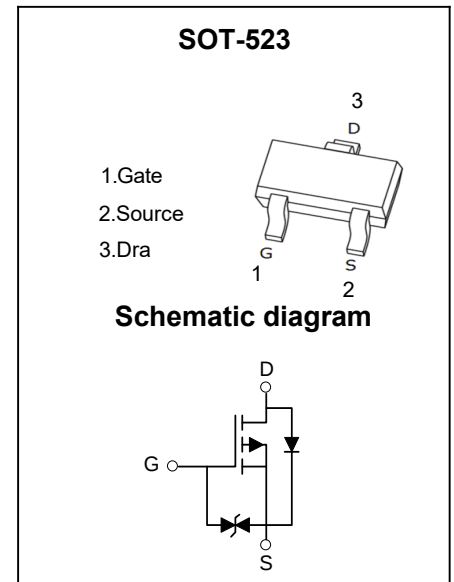
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-30V	470mΩ@-10V	-0.45A
	680mΩ@-4.5V	

Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- ESD Protected

Application

- Load Switching
- Low Current Inverters
- Low Current DC/DC Converters



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	-30	V
Gate - Source Voltage		V_{GS}	±12	V
Continuous Drain Current ^{1,5}	$T_A = 25^\circ\text{C}$	I_D	-0.45	A
Pulsed Drain Current ²		I_{DM}	-1.8	A
Power Dissipation ^{4,5}	$T_A = 25^\circ\text{C}$	P_D	0.25	W
Thermal Resistance from Junction to Ambient ⁵		$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

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MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

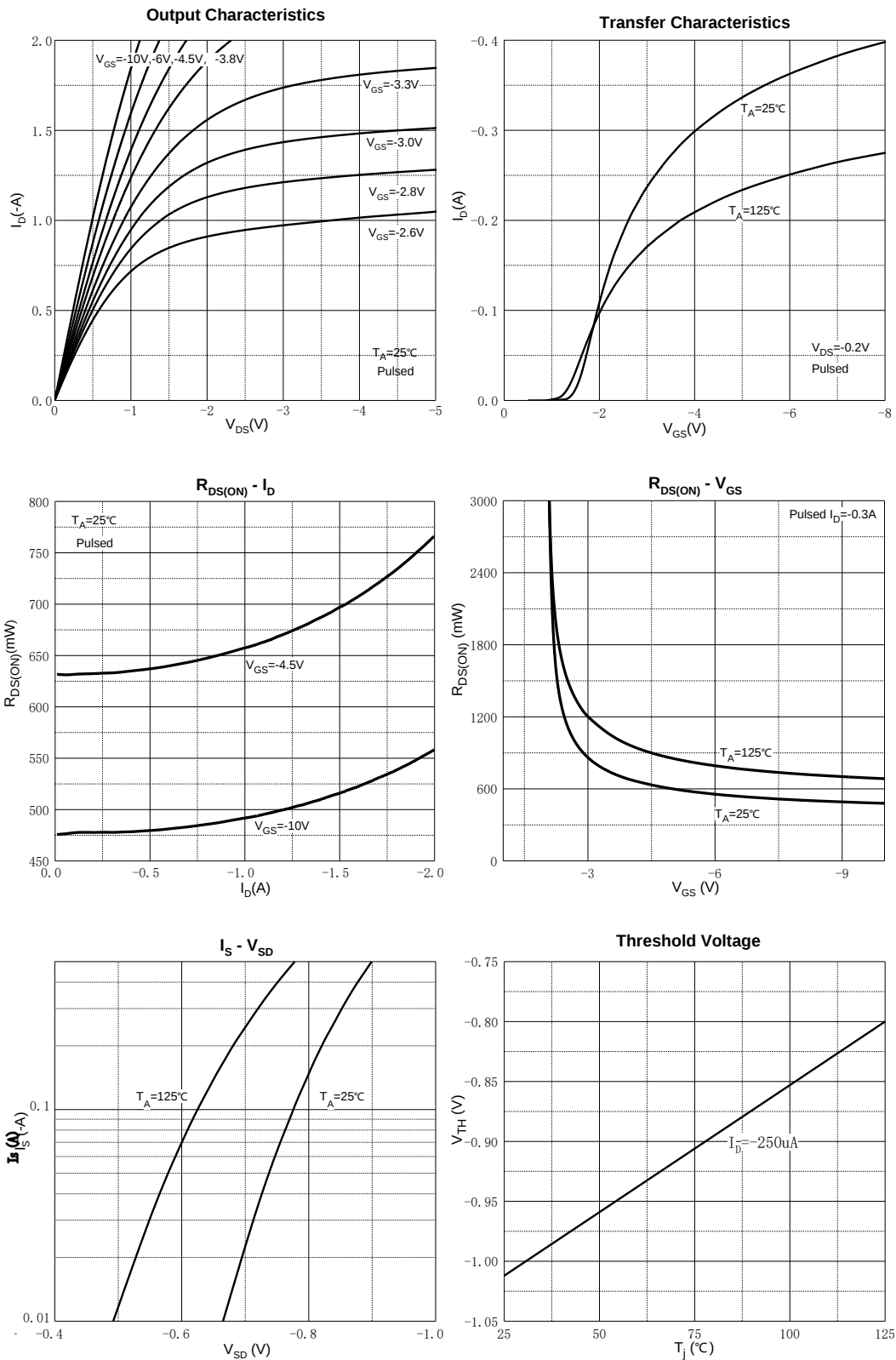
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 10	μA
On Characteristics ³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	-0.5	-1	-1.5	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -0.3A$		470	800	m Ω
		$V_{GS} = -4.5V, I_D = -0.3A$		680	900	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		48.4		pF
Output Capacitance	C_{oss}			9.8		
Reverse Transfer Capacitance	C_{rss}			5.2		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		11.2		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -15V, V_{GS} = -10V, I_D = -0.6A$		1.94		nC
Gate-source Charge	Q_{gs}			0.65		
Gate-drain Charge	Q_{gd}			0.01		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15V, V_{GS} = -4.5V,$ $R_L = 47\Omega, R_G = 10\Omega$		6.5		ns
Turn-on Rise Time	t_r			6.5		
Turn-off Delay Ttime	$t_{d(off)}$			18.2		
Turn-off Fall Time	t_f			5.5		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -0.3A$			-1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

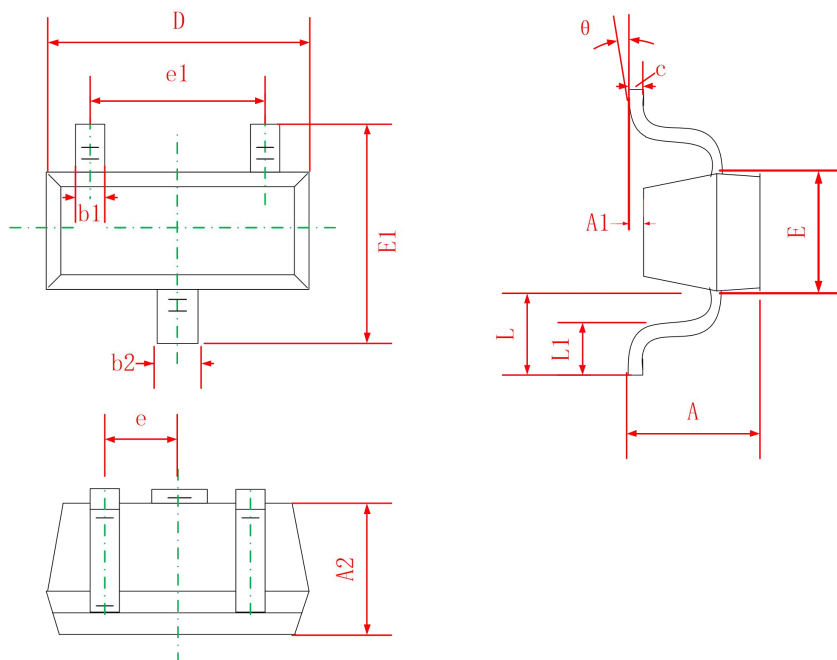
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Typical Characteristics



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SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°

SOT-523 Suggested Pad Layout

